

Silicon NPN Power Transistors

2N3234

DESCRIPTION

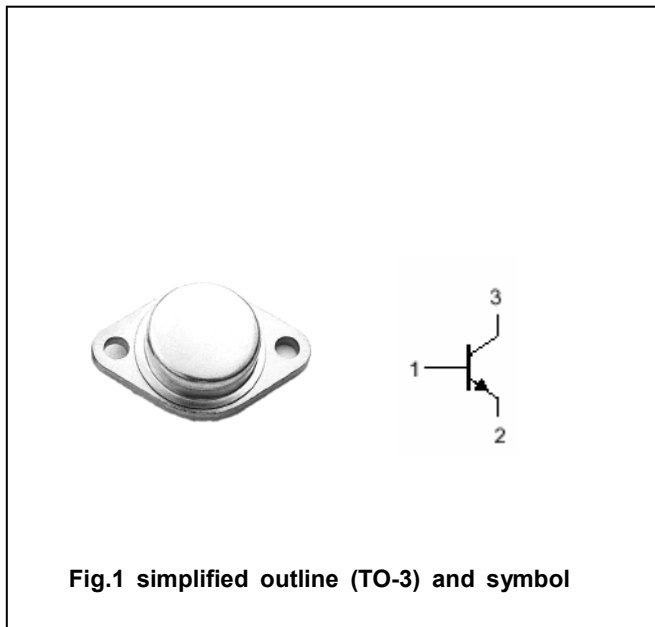
- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For audio amplifier and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	160	V
V _{CEO}	Collector-emitter voltage	Open base	160	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		7.5	A
P _C	Collector power dissipation	T _C =25°C	115	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{(th) jc}	Thermal resistance junction to case	1.17	°C/W

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CHARACTERISTICS

 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=30\text{mA}; I_B=0$	160			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			1.0	V
$V_{BE(on)}$	Base-emitter on voltage	$I_C=3\text{A}; V_{CE}=4\text{V}$			1.5	V
I_{CEO}	Collector cut-off current	$V_{CE}=80\text{V}; I_B=0$			0.7	mA
I_{CBO}	Collector cut-off current	$V_{CB}=160\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7\text{V}; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=5\text{A}; V_{CE}=10\text{V}$	18		55	

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PACKAGE OUTLINE

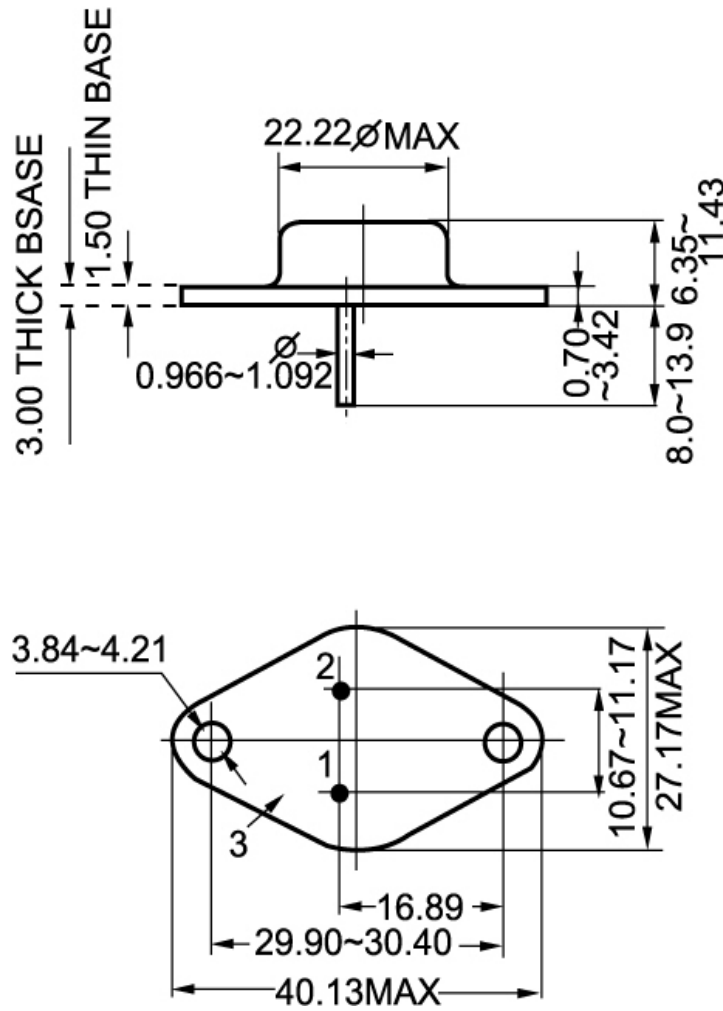


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)